优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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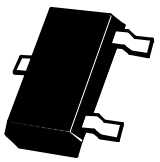
SUMMARY

$V_{(BR)DSS}$=20V; $R_{DS(ON)}$=0.18Ω; I_D=1.7A



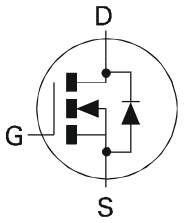
SOT23

DESCRIPTION

This new generation of high density MOSFETs from Zetex utilises a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.

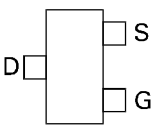
FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- SOT23 package



APPLICATIONS

- DC - DC Converters
- Power Management Functions
- Disconnect switches
- Motor control



Top View

ORDERING INFORMATION

DEVICE	REEL SIZE (inches)	TAPE WIDTH (mm)	QUANTITY PER REEL
NK-ZXM61N02FTA	7	8mm embossed	3000 units
NK-ZXM61N02FTC	13	8mm embossed	10000 units

DEVICE MARKING

- N02

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DSS}	20	V
Gate Source Voltage	V_{GS}	± 12	V
Continuous Drain Current (V_{GS}=4.5V; T_A=25°C)(b) (V_{GS}=4.5V; T_A=70°C)(b)	I_D	1.7 1.3	A
Pulsed Drain Current (c)	I_{DM}	7.4	A
Continuous Source Current (Body Diode) (b)	I_S	0.8	A
Pulsed Source Current (Body Diode)	I_{SM}	7.4	A
Power Dissipation at T_A=25°C (a) Linear Derating Factor	P_D	625 5	mW mW/°C
Power Dissipation at T_A=25°C (b) Linear Derating Factor	P_D	806 6.4	mW mW/°C
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +150	°C

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	200	°C/W
Junction to Ambient (b)	$R_{\theta JA}$	155	°C/W

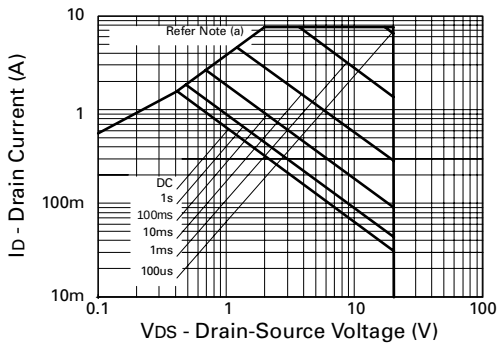
NOTES

(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

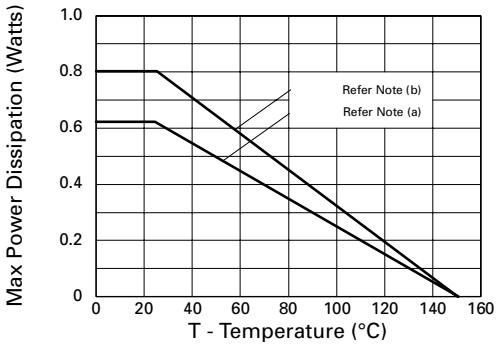
(b) For a device surface mounted on FR4 PCB measured at t≤5 secs.

(c) Repetitive rating - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

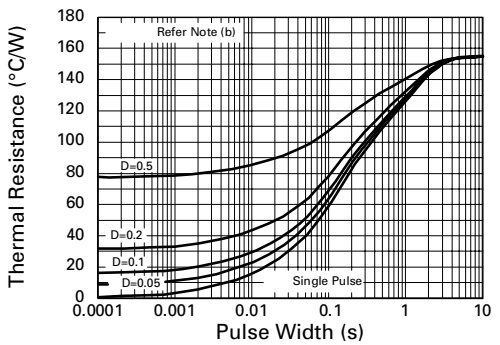
CHARACTERISTICS



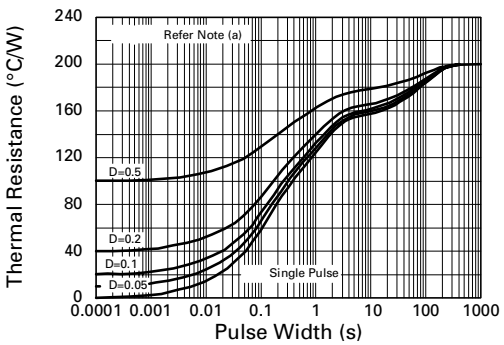
Safe Operating Area



Derating Curve



Transient Thermal Impedance



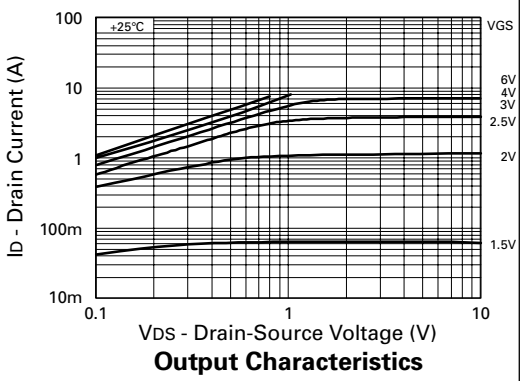
Transient Thermal Impedance

ELECTRICAL CHARACTERISTICS (at T_A = 25°C unless otherwise stated).

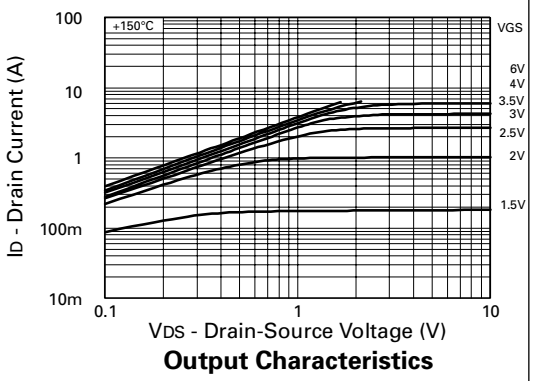
PARAMETER	SYMBOL	MIN.	TYP.(3)	MAX.	UNIT	CONDITIONS.
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	20			V	I_D=250μA, V_{GS}=0V
Zero Gate Voltage Drain Current	I_{DSS}			1	μA	V_{DS}=20V, V_{GS}=0V
Gate-Body Leakage	I_{GSS}			100	nA	V_{GS}=± 12V, V_{DS}=0V
Gate-Source Threshold Voltage	$V_{GS(th)}$	0.7			V	I_D=250μA, V_{DS}= V_{GS}
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$			0.18 0.24	Ω Ω	V_{GS}=4.5V, I_D=0.93A V_{GS}=2.7V, I_D=0.47A
Forward Transconductance (3)	g_{fs}	1.3			S	V_{DS}=10V,I_D=0.47A
DYNAMIC (3)						
Input Capacitance	C_{iss}		160		pF	V_{DS}=15 V, V_{GS}=0V, f=1MHz
Output Capacitance	C_{oss}		50		pF	
Reverse Transfer Capacitance	C_{rss}		30		pF	
SWITCHING(2) (3)						
Turn-On Delay Time	$t_{d(on)}$		2.4		ns	V_{DD}=10V, I_D=0.93A R_G=6.2Ω, R_D=11Ω (refer to test circuit)
Rise Time	t_r		4.2		ns	
Turn-Off Delay Time	$t_{d(off)}$		7.8		ns	
Fall Time	t_f		4.2		ns	
Total Gate Charge	Q_g			3.4	nC	V_{DS}=16V,V_{GS}=4.5V, I_D=0.93A (refer to test circuit)
Gate-Source Charge	Q_{gs}			0.41	nC	
Gate-Drain Charge	Q_{gd}			0.8	nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V_{SD}			0.95	V	T_J=25°C, I_S=0.93A, V_{GS}=0V
Reverse Recovery Time (3)	t_{rr}		12.9		ns	T_J=25°C, I_F=0.93A, di/dt= 100A/μs
Reverse Recovery Charge (3)	Q_{rr}		5.2		nC	

NOTES
(1) Measured under pulsed conditions. Width≤300μs. Duty cycle ≤2% .
(2) Switching characteristics are independent of operating junction temperature.
(3) For design aid only, not subject to production testing.

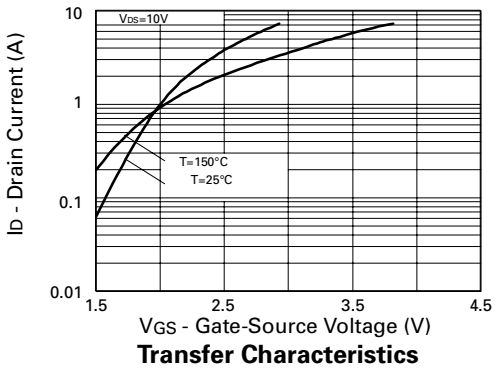
TYPICAL CHARACTERISTICS



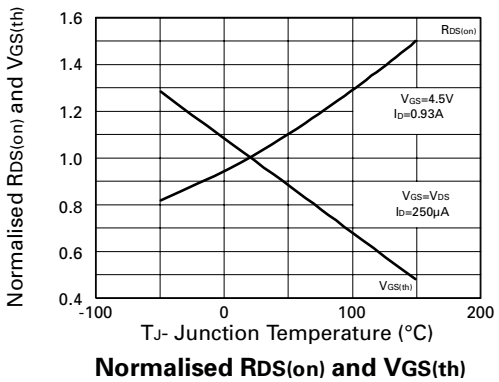
Output Characteristics



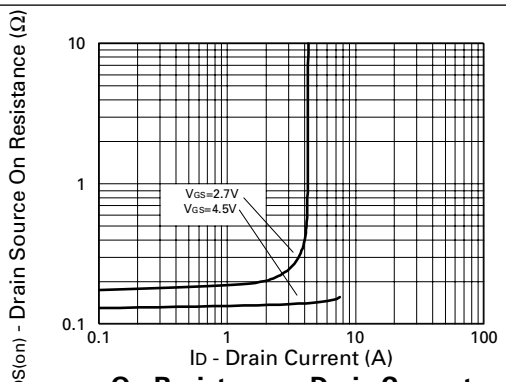
Output Characteristics



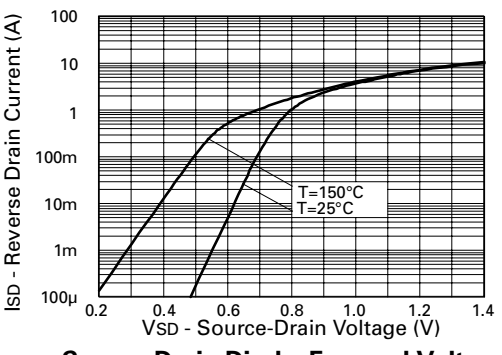
Transfer Characteristics



Normalised RDS(on) and VGS(th) v Temperature

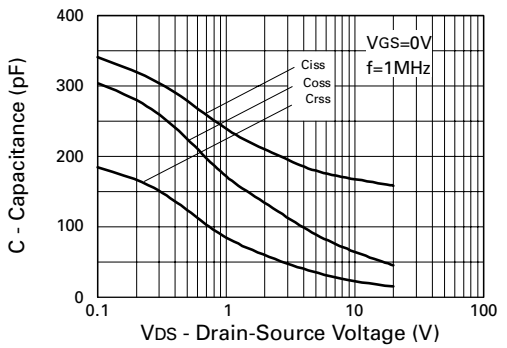


On-Resistance v Drain Current

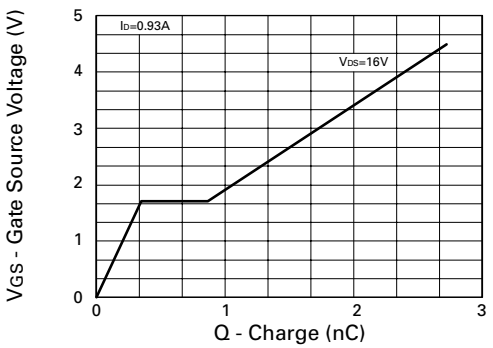


Source-Drain Diode Forward Voltage

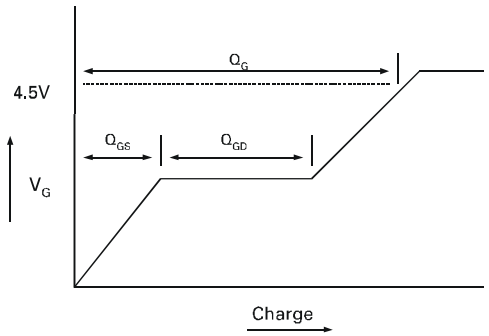
TYPICAL CHARACTERISTICS



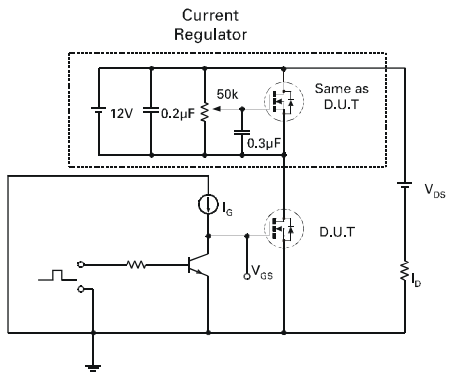
Capacitance v Drain-Source Voltage



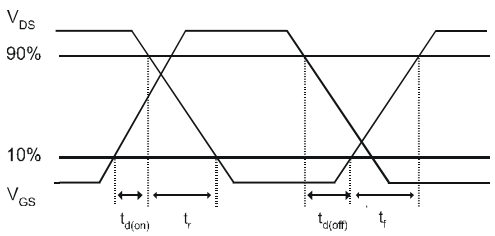
Gate-Source Voltage v Gate Charge



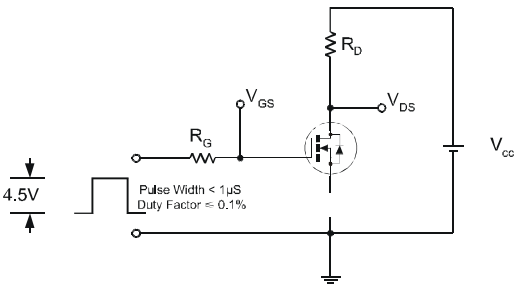
Basic Gate Charge Waveform



Gate Charge Test Circuit



Switching Time Waveforms



Switching Time Test Circuit